

FIG. 1A  
(PRIOR ART)

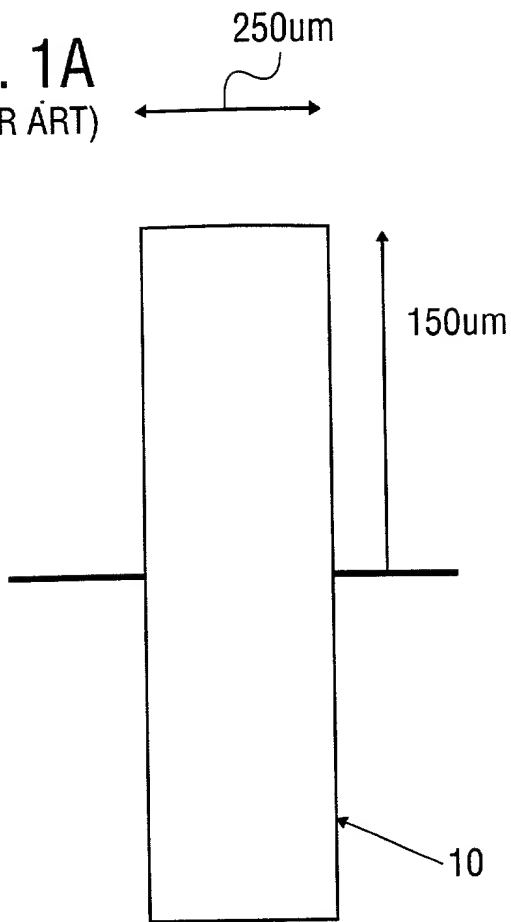


FIG. 1B  
(PRIOR ART)

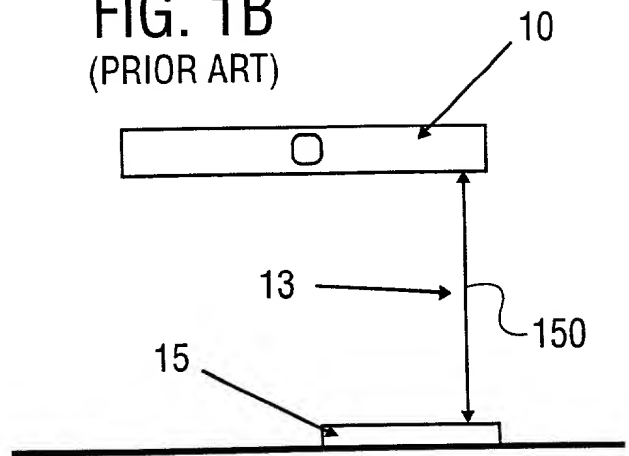
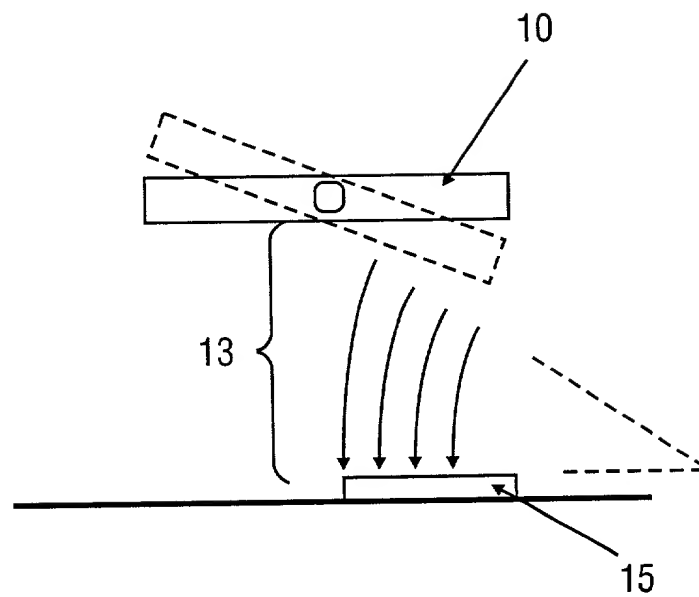


FIG. 1C  
(PRIOR ART)



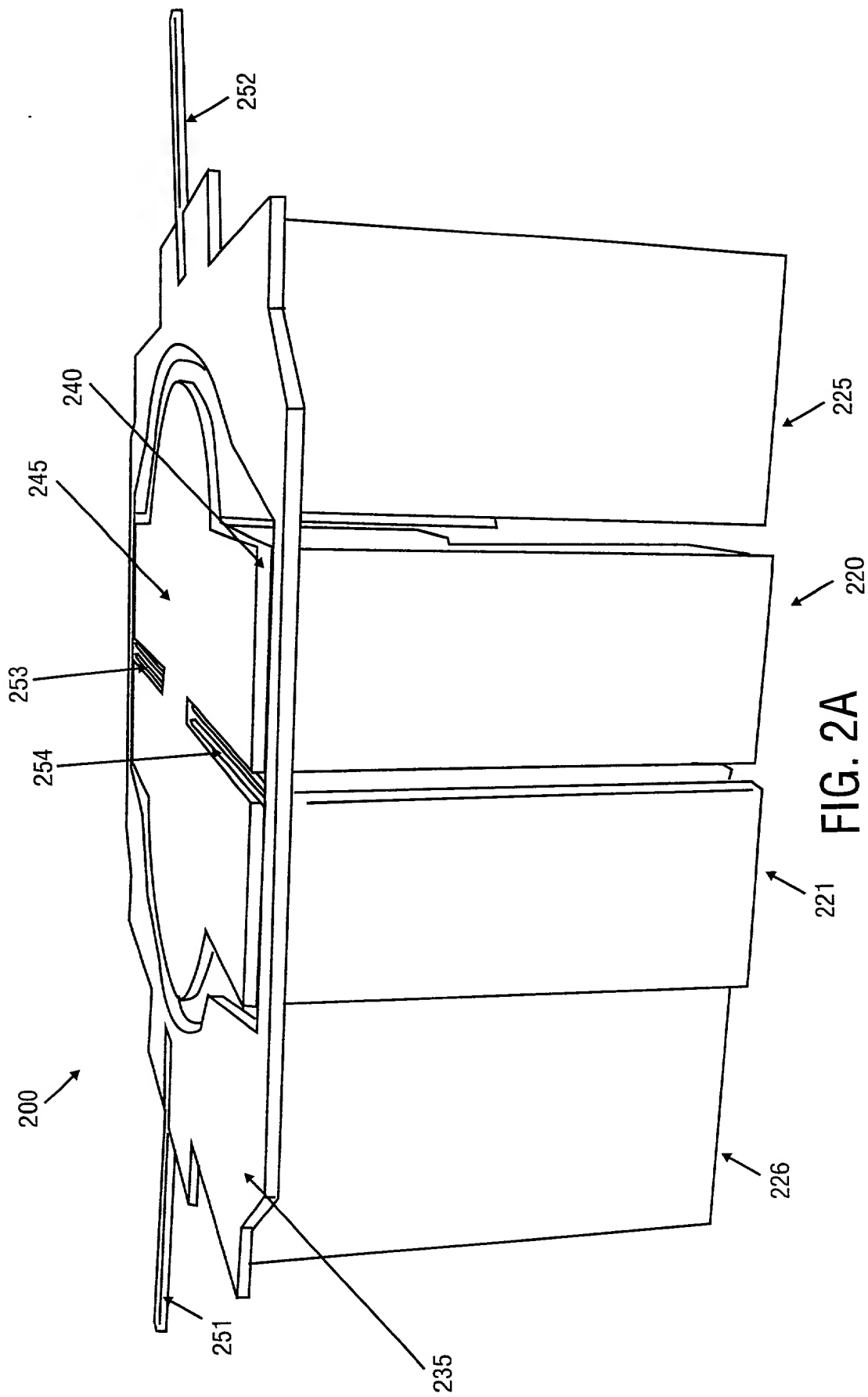




FIG. 3A

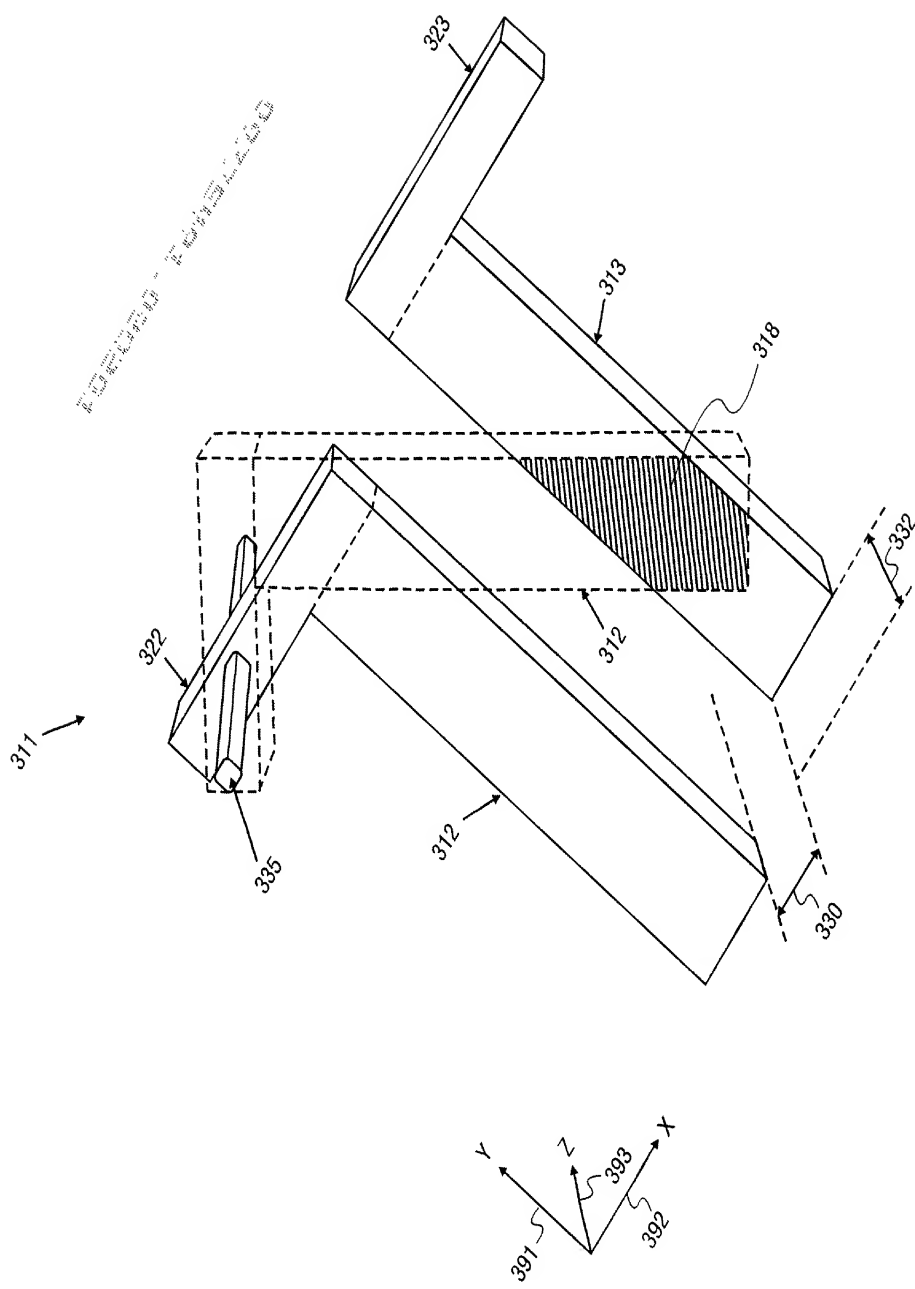


FIG. 3B

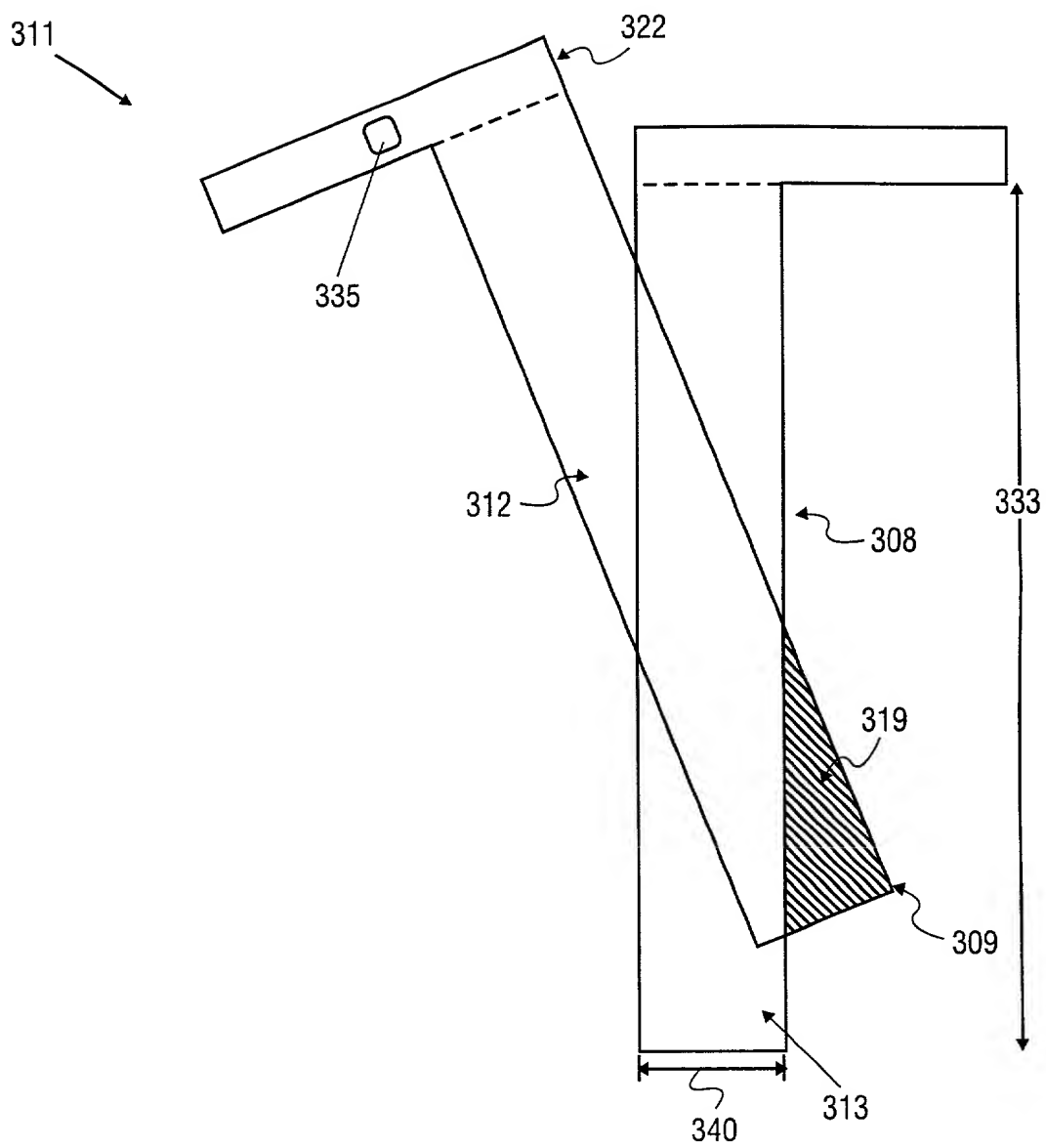


FIG. 3C

FIG. 3D is a schematic diagram of a device 300 in a second state. The device 300 includes a first portion 310 and a second portion 320. The first portion 310 is a rectangular block. The second portion 320 is a rectangular block that is positioned to the right of the first portion 310. A vertical line 335 is positioned to the left of the first portion 310. A horizontal line 340 is positioned between the first portion 310 and the second portion 320. A dashed line 330 is positioned between the first portion 310 and the second portion 320. A dashed line 332 is positioned between the first portion 310 and the second portion 320. A dashed line 313 is positioned between the first portion 310 and the second portion 320. A dashed line 314 is positioned between the first portion 310 and the second portion 320.

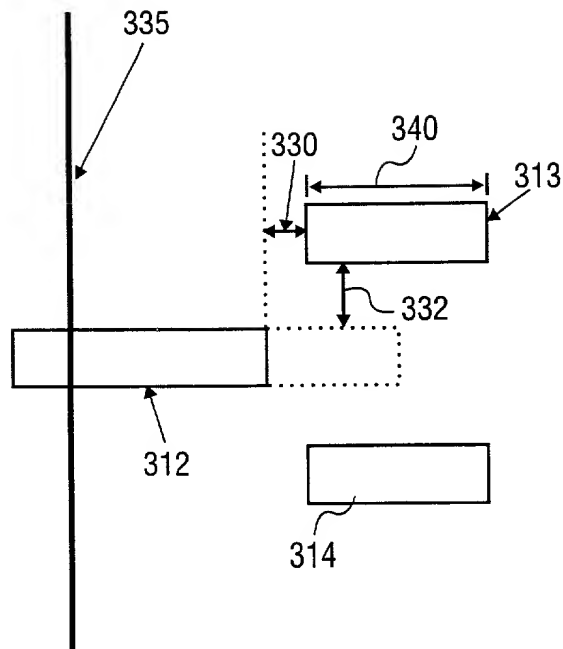
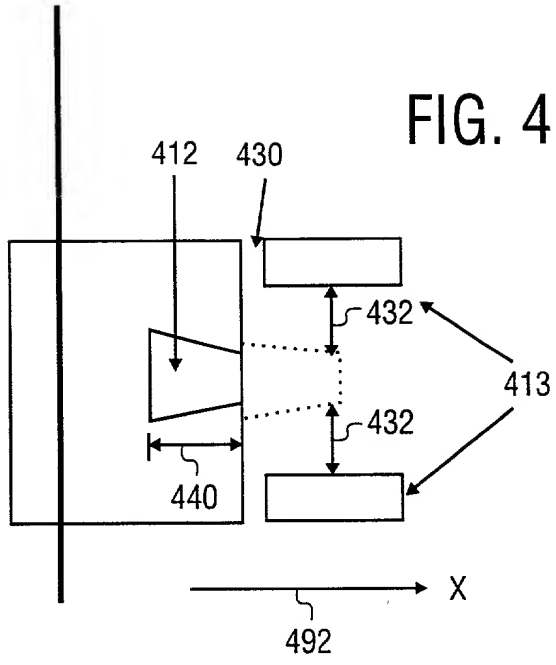


FIG. 3D





FIG. 4 is a schematic diagram of a device 400 in a cross-sectional view. The device 400 includes a substrate 410, a gate stack 412, a gate electrode 413, a channel layer 414, a source/drain region 415, and a contact layer 416. The gate stack 412 is formed on the substrate 410 and includes a gate oxide layer 412a and a gate electrode layer 412b. The gate electrode 413 is formed on the gate stack 412 and is electrically connected to the gate oxide layer 412a. The channel layer 414 is formed on the gate electrode 413 and is electrically connected to the gate electrode layer 412b. The source/drain region 415 is formed on the channel layer 414 and is electrically connected to the channel layer 414. The contact layer 416 is formed on the source/drain region 415 and is electrically connected to the source/drain region 415. The device 400 is shown in a cross-sectional view along a line X-X'.



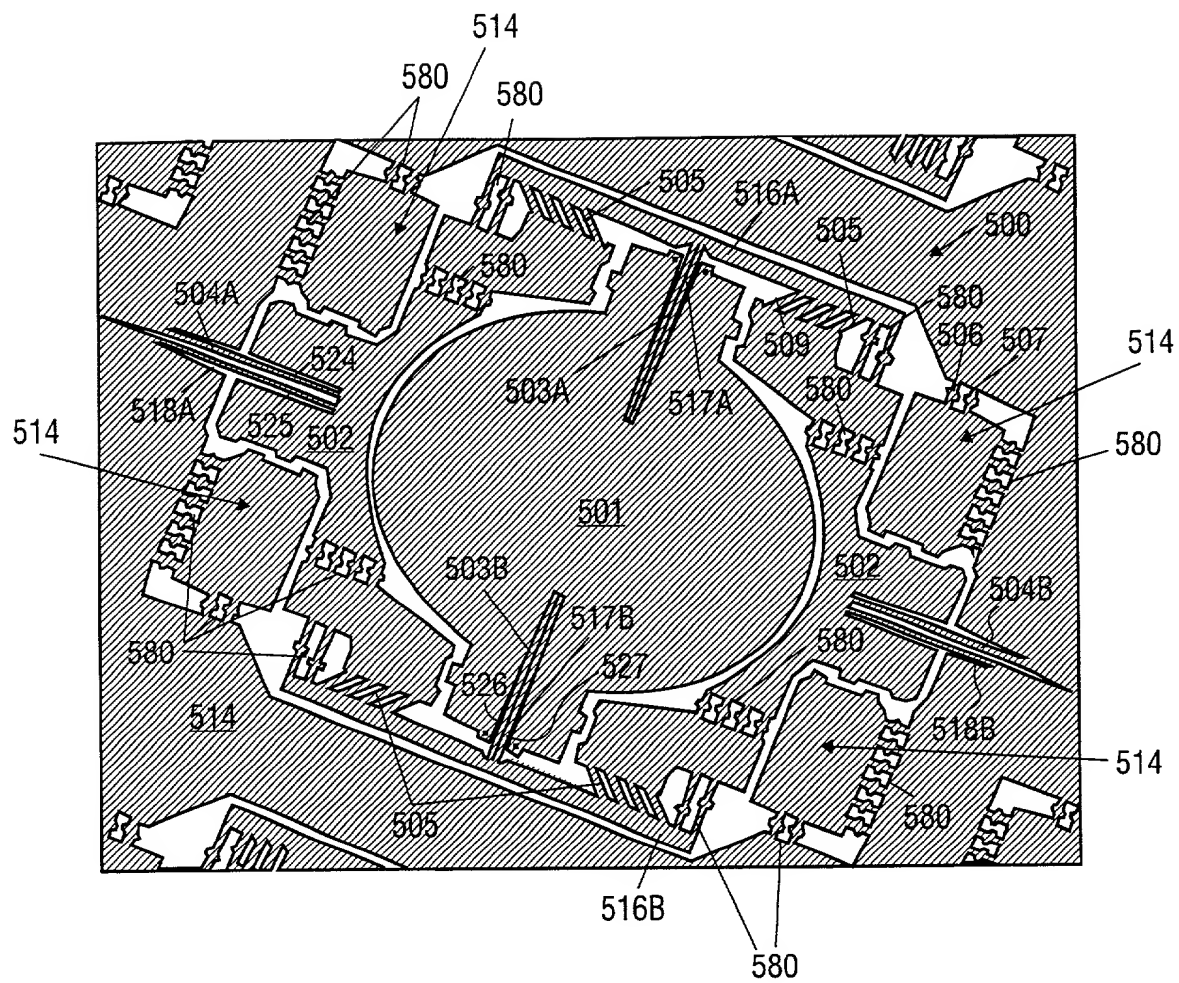


FIG. 5A

FIG. 5B is a cross-sectional view of the device 500, showing the device 500 in a first position. The device 500 includes a base 501, a support 502, a shaft 503, a handle 504, and a tip 505. The device 500 is shown in a first position, where the tip 505 is positioned at the top of the shaft 503. The device 500 is shown in a second position, where the tip 505 is positioned at the bottom of the shaft 503. The device 500 is shown in a third position, where the tip 505 is positioned at the side of the shaft 503. The device 500 is shown in a fourth position, where the tip 505 is positioned at the front of the shaft 503. The device 500 is shown in a fifth position, where the tip 505 is positioned at the back of the shaft 503. The device 500 is shown in a sixth position, where the tip 505 is positioned at the top of the shaft 503. The device 500 is shown in a seventh position, where the tip 505 is positioned at the bottom of the shaft 503. The device 500 is shown in an eighth position, where the tip 505 is positioned at the side of the shaft 503. The device 500 is shown in a ninth position, where the tip 505 is positioned at the front of the shaft 503. The device 500 is shown in a tenth position, where the tip 505 is positioned at the back of the shaft 503.

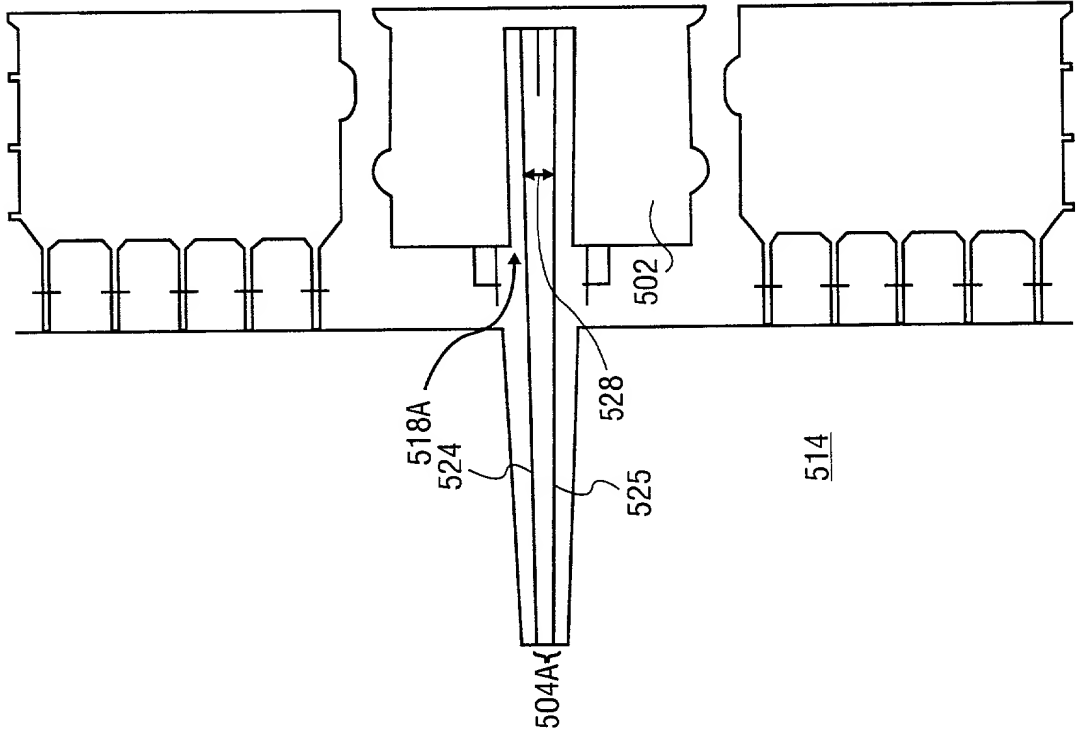


FIG. 5B

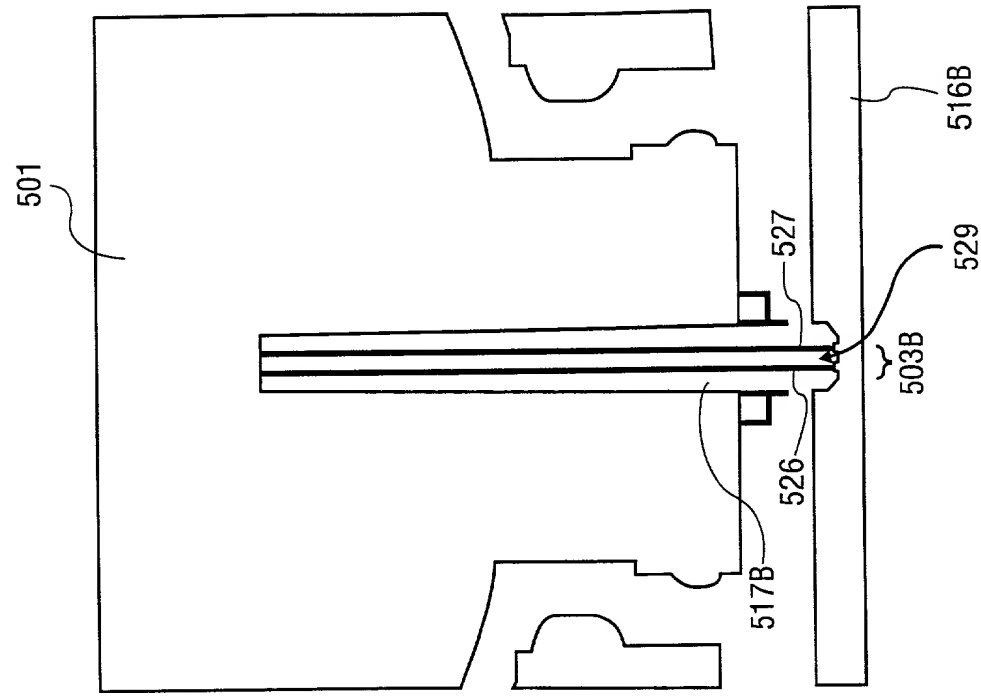


FIG. 5C

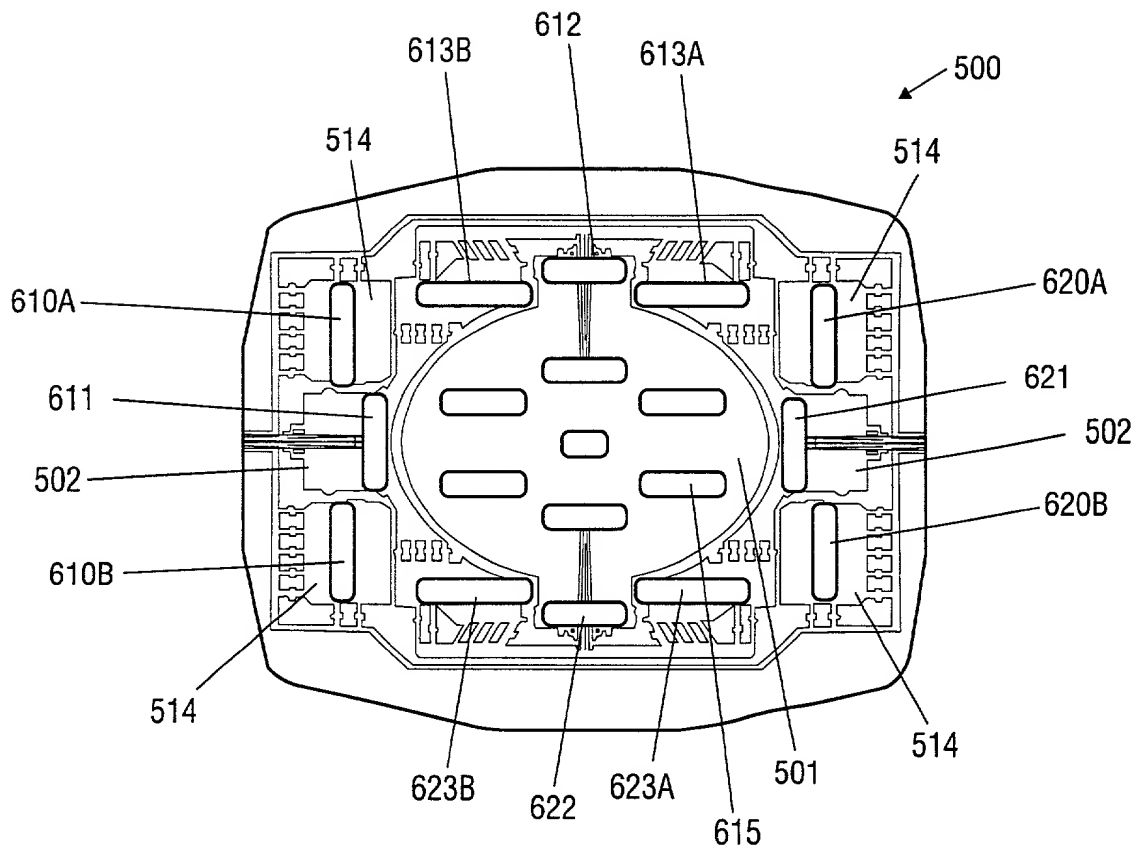


FIG. 6

FIG. 7A is a top view of a semiconductor device 700. The device 700 includes a substrate 701, a gate stack 702, a source/drain region 703, a gate electrode 704, a gate spacer 705, a gate contact 706, a gate pad 707, a gate line 708, a gate bus 709, a gate pad 710, a gate contact 711, a gate spacer 712, a gate electrode 713, a source/drain region 714, a gate stack 715, and a substrate 716.

700

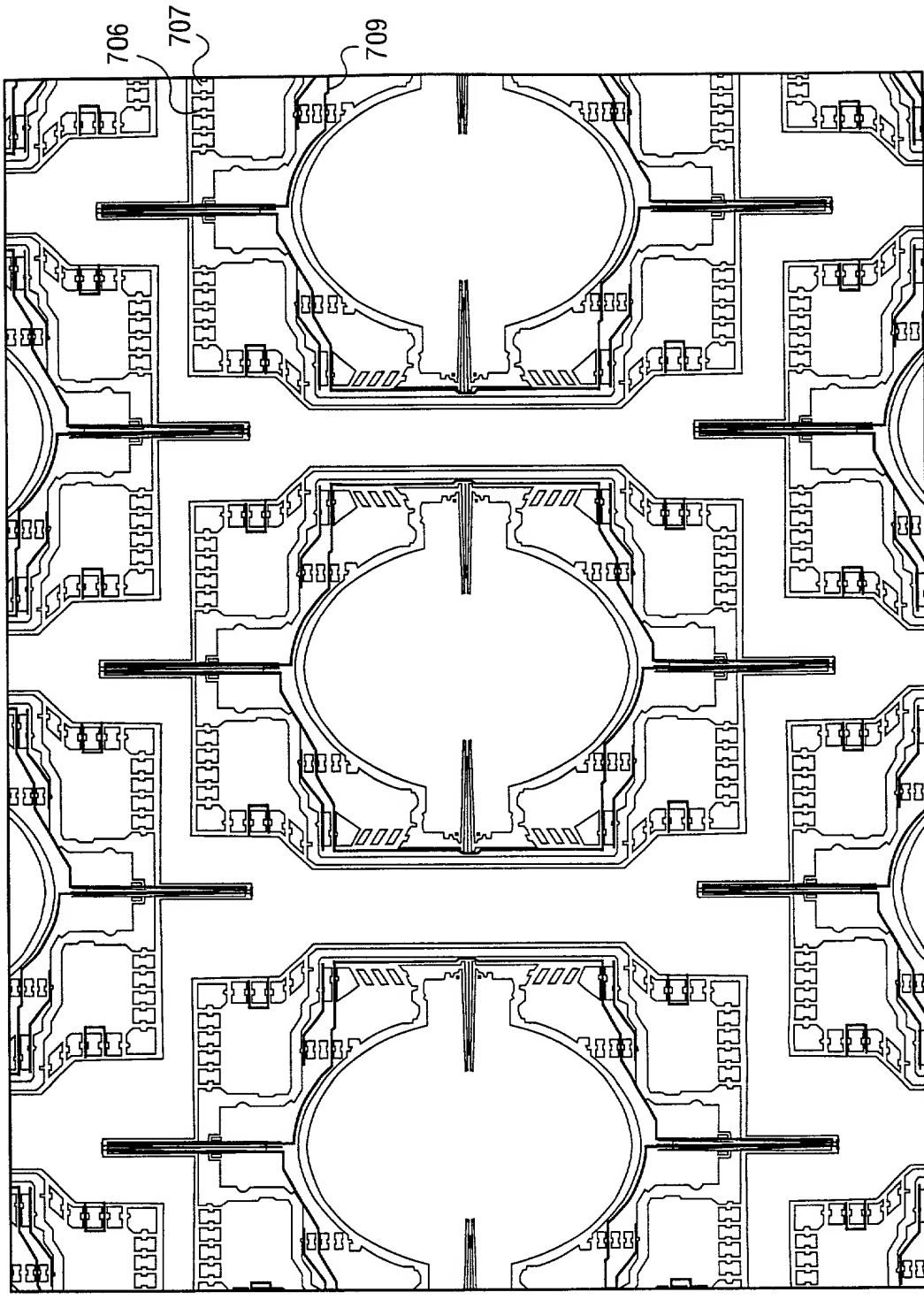


FIG. 7A

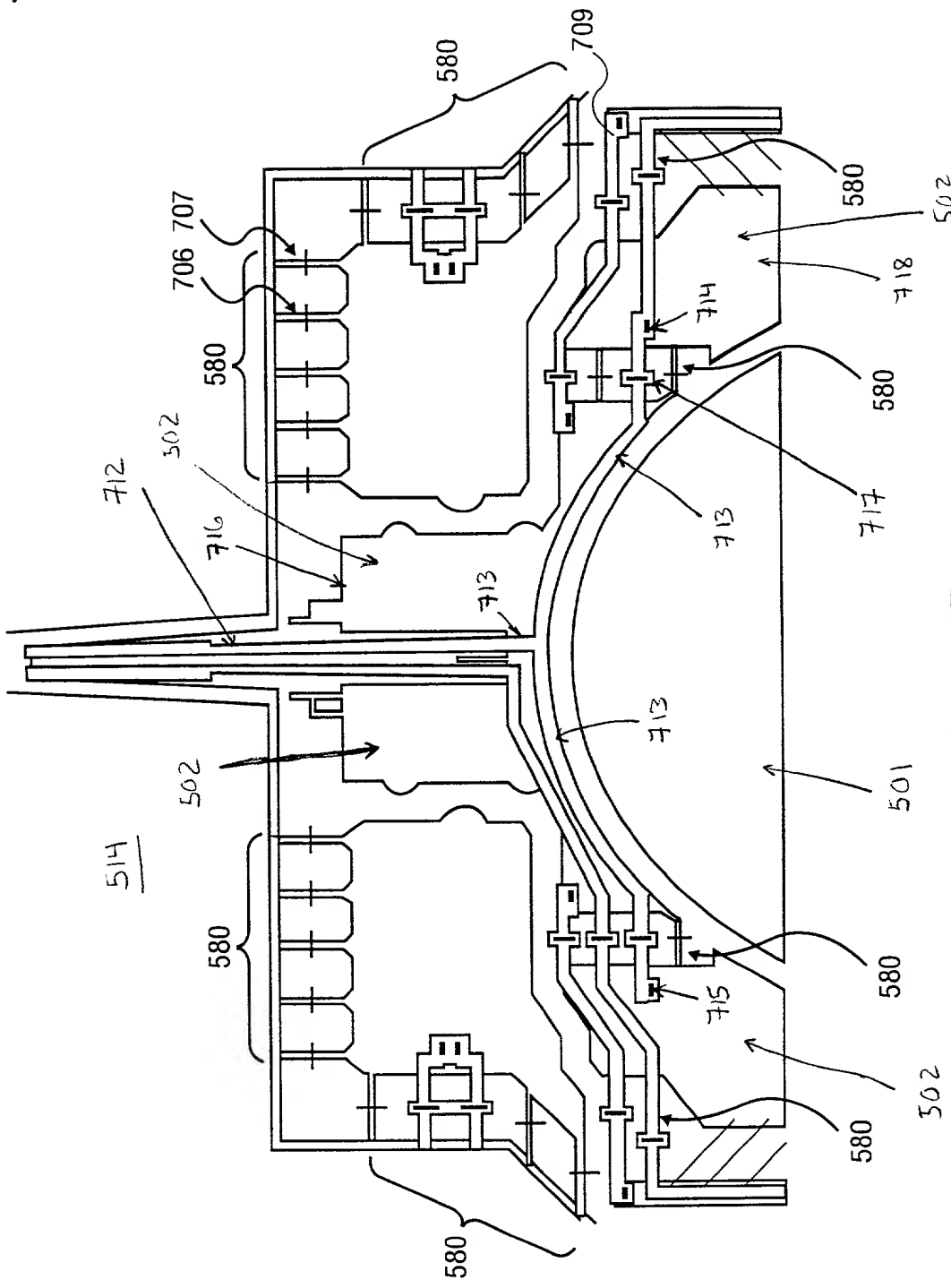


FIG. 7B

FIG. 8 is a top view of a device 500, which is a cross-sectional view of a device 500, showing a central circular region 801, surrounded by a ring of eight rectangular regions 9A-9K, which are arranged in a circular pattern around the central region 801. The device 500 is shown in a cross-sectional view, with the central region 801 being a circular region, and the surrounding regions 9A-9K being rectangular regions arranged in a circular pattern around the central region 801. The device 500 is shown in a cross-sectional view, with the central region 801 being a circular region, and the surrounding regions 9A-9K being rectangular regions arranged in a circular pattern around the central region 801.

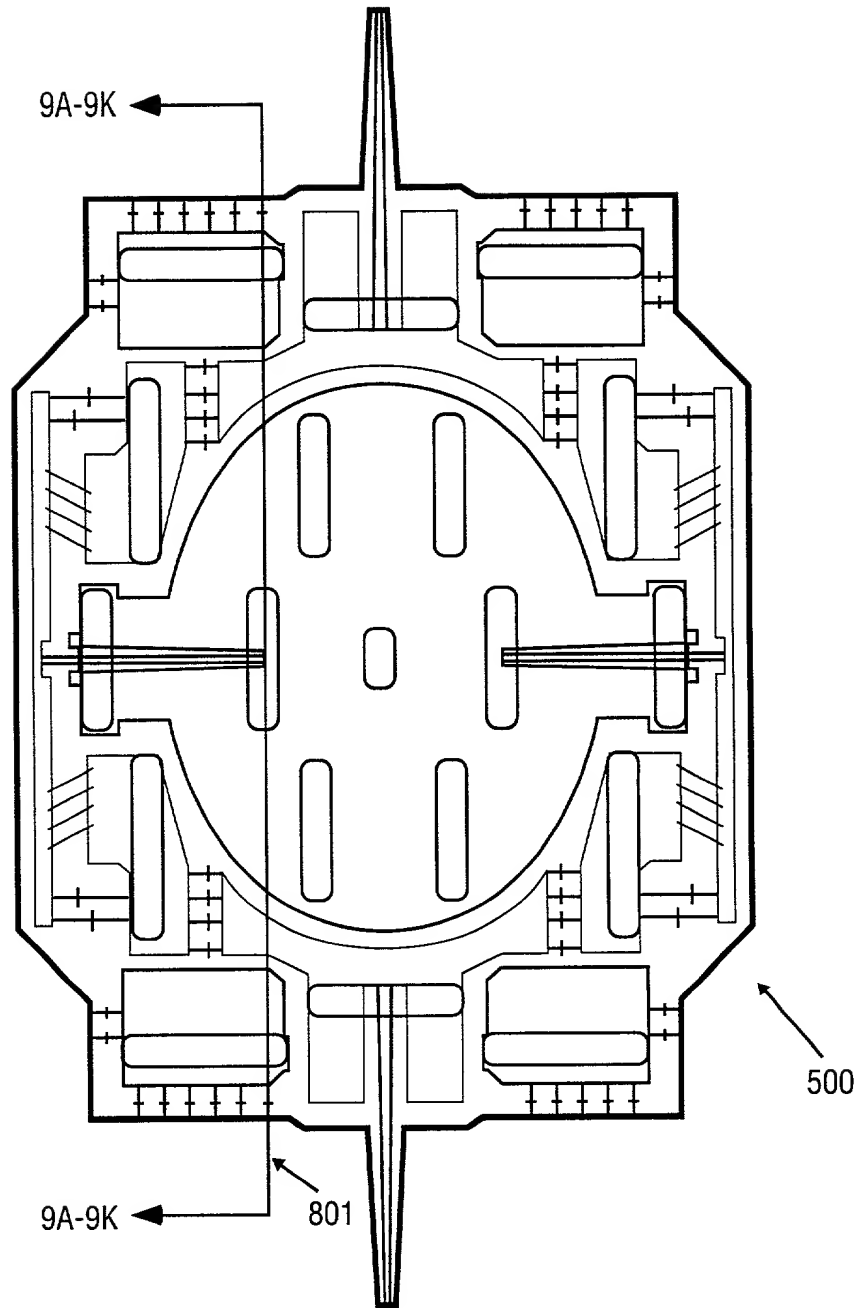


FIG. 8

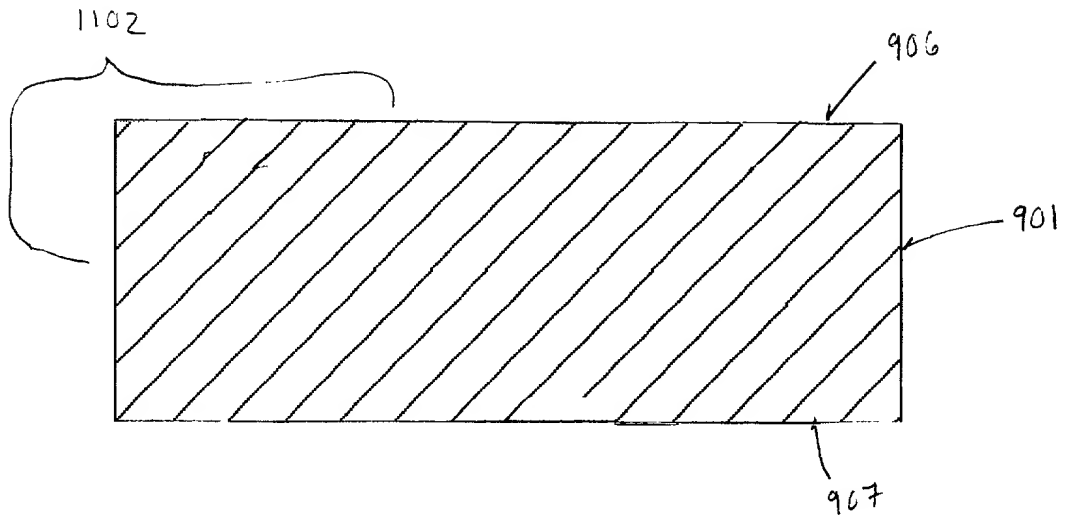


FIG. 9 A



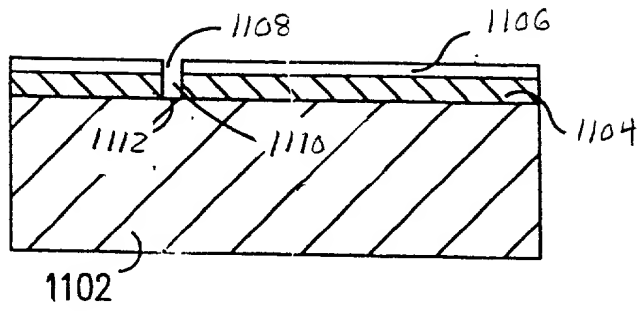


FIG. 9B

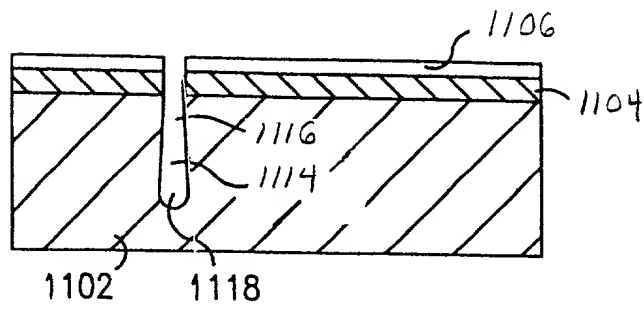


FIG. 9C

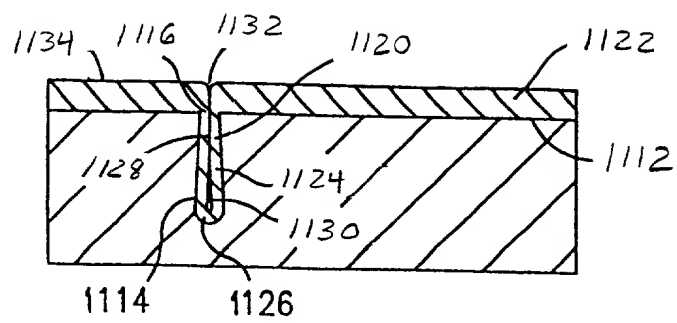


FIG. 9D

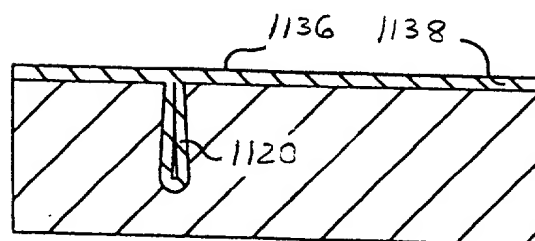
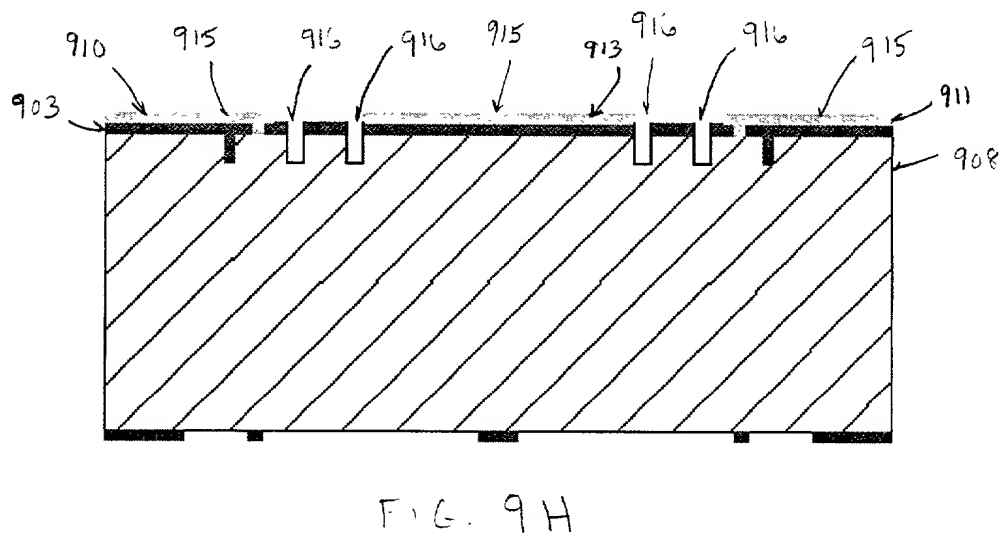
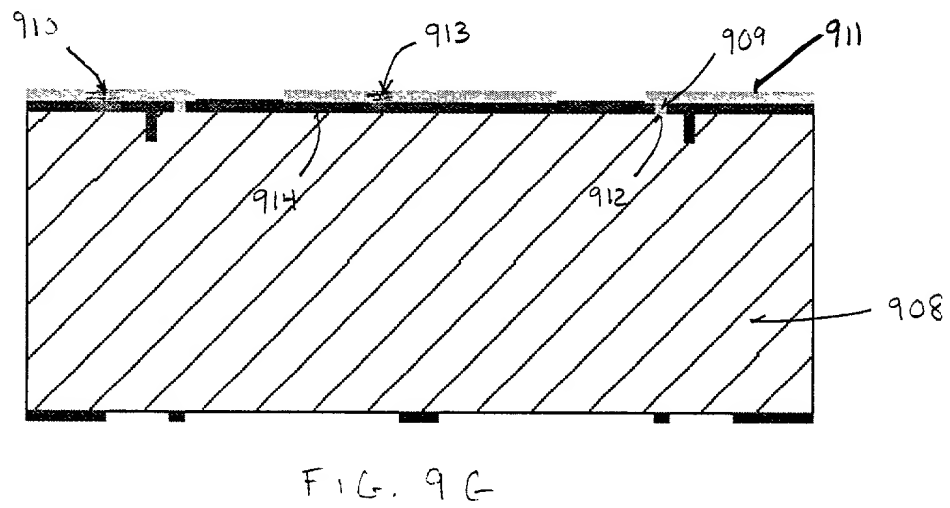
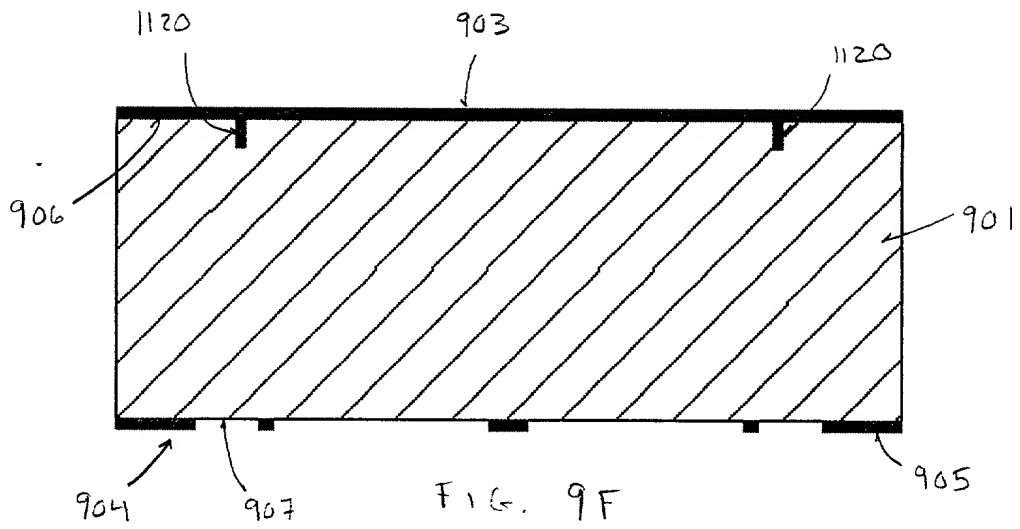
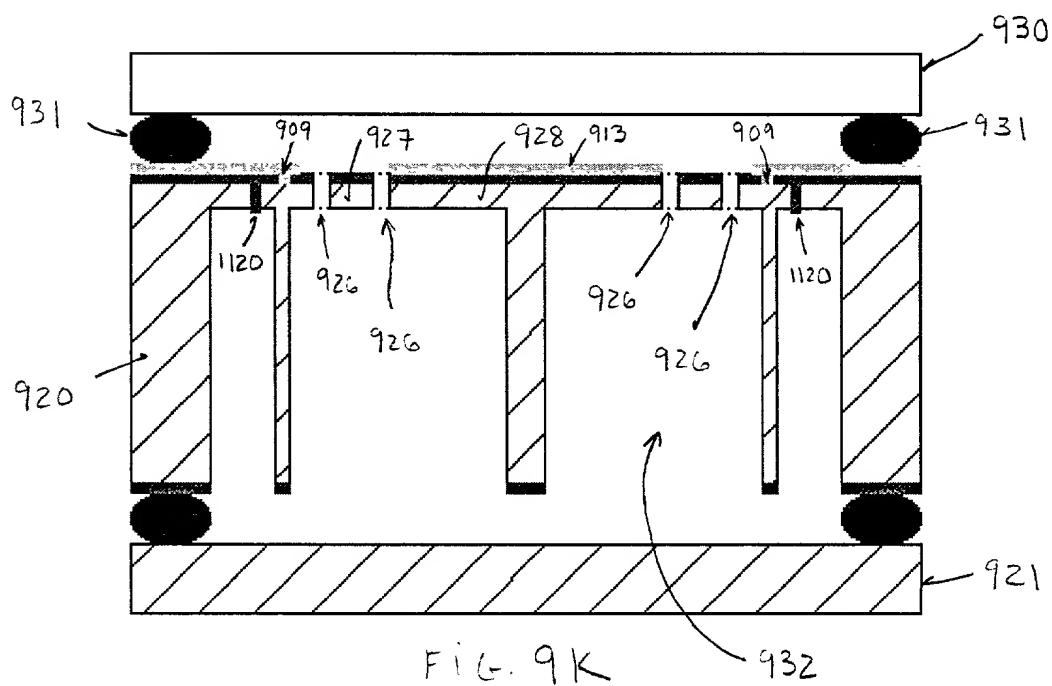
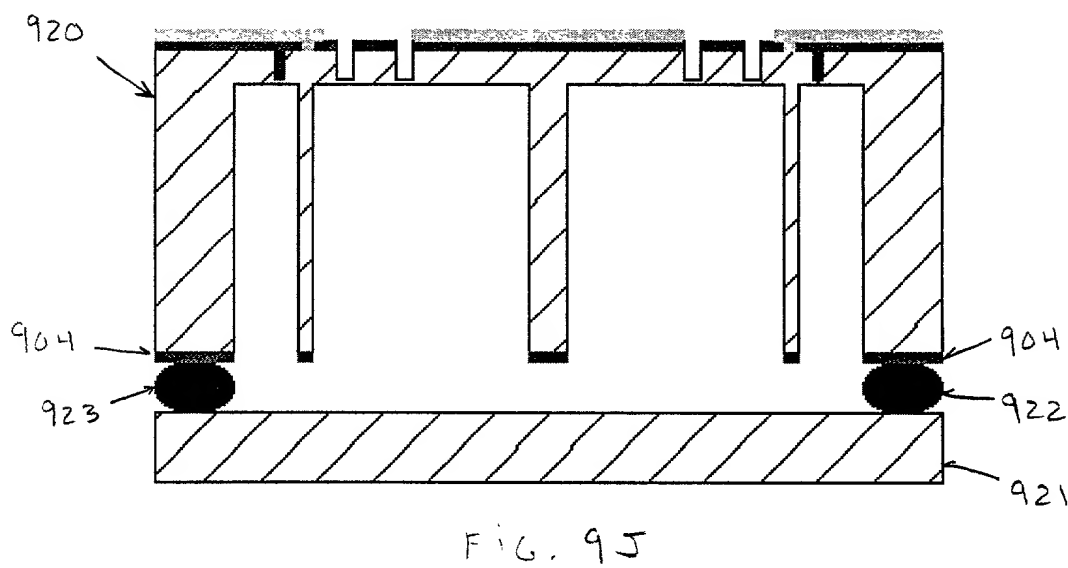
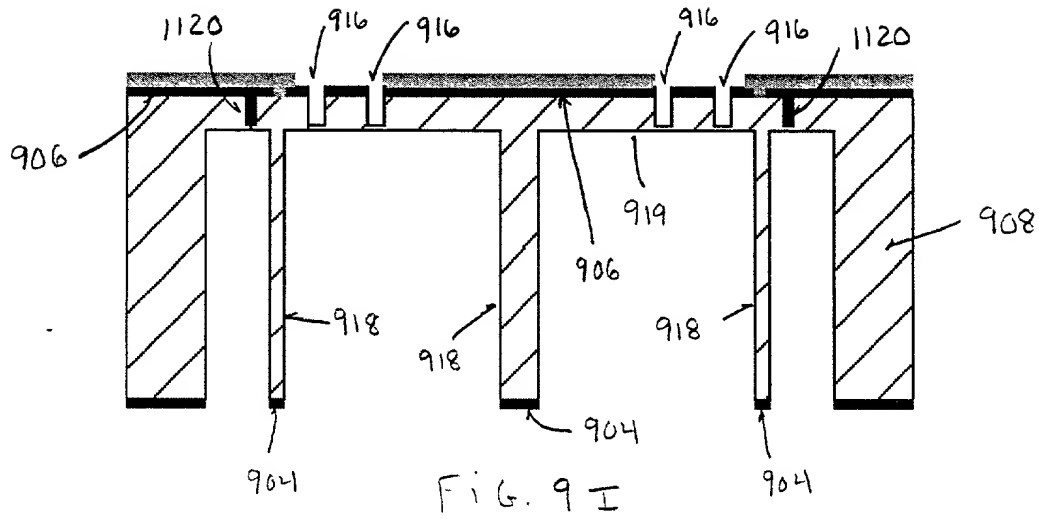


FIG. 9E





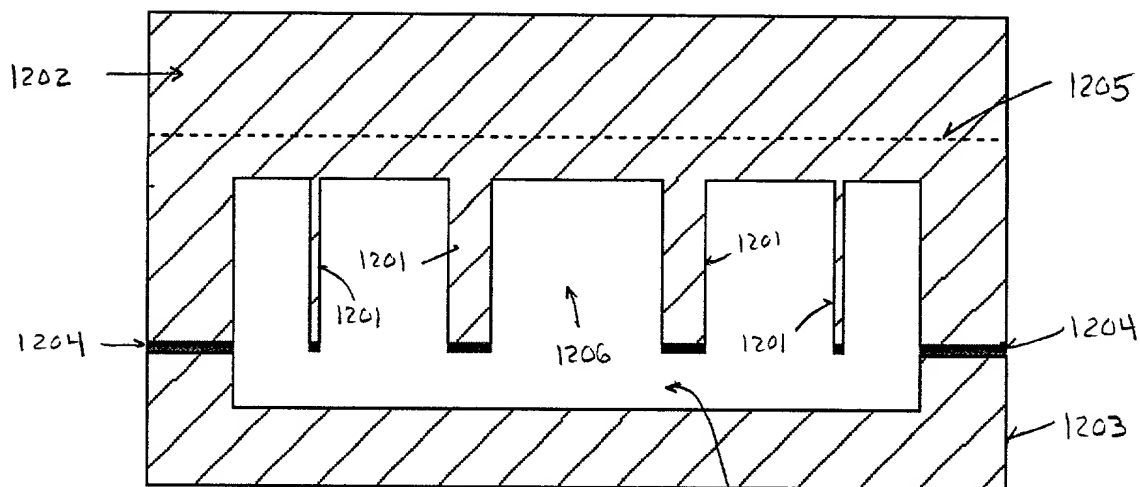


FIG. 10A

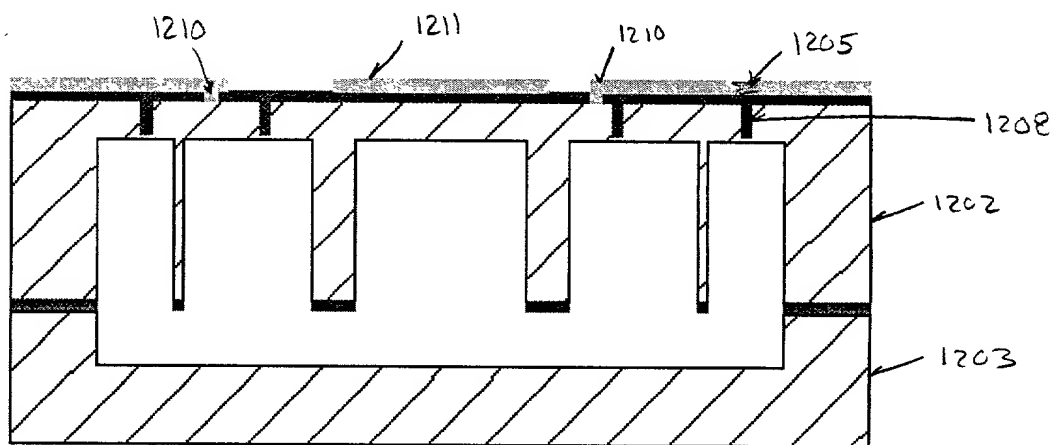


FIG. 10B

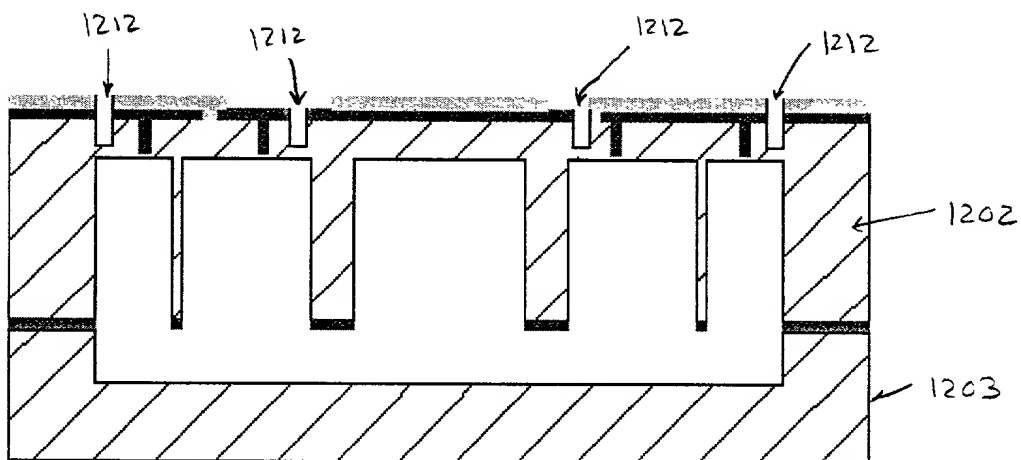


FIG. 10C

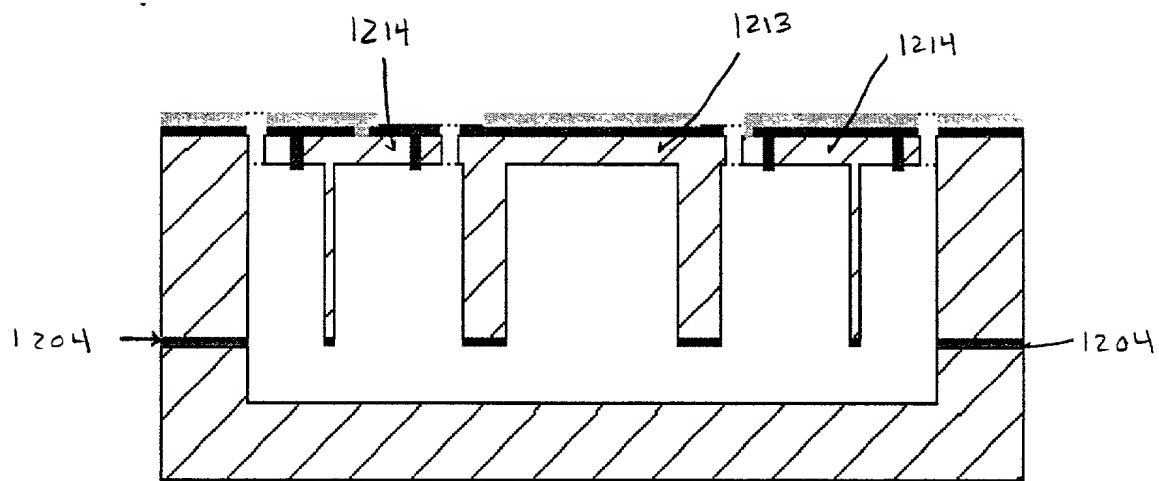


FIG. 10D

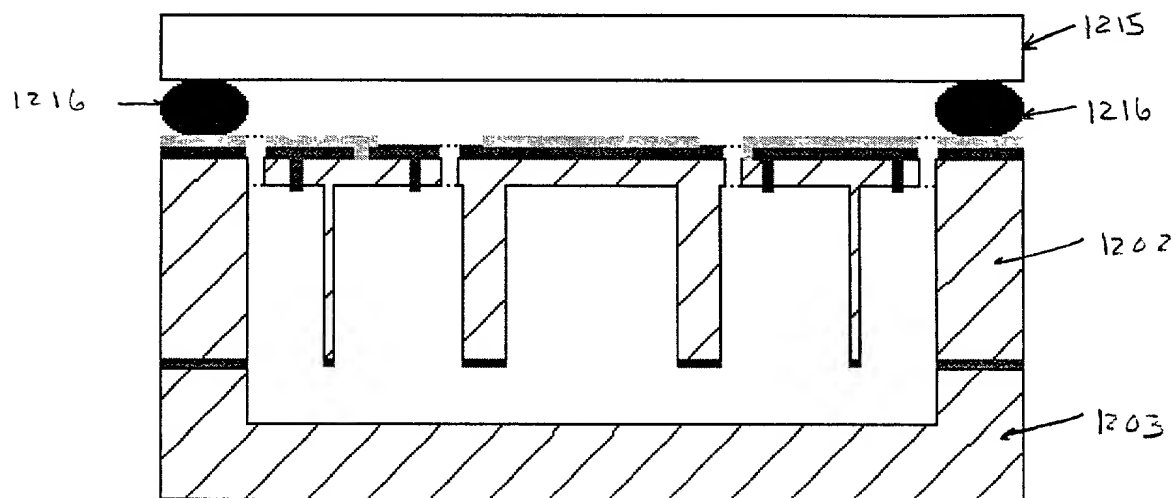
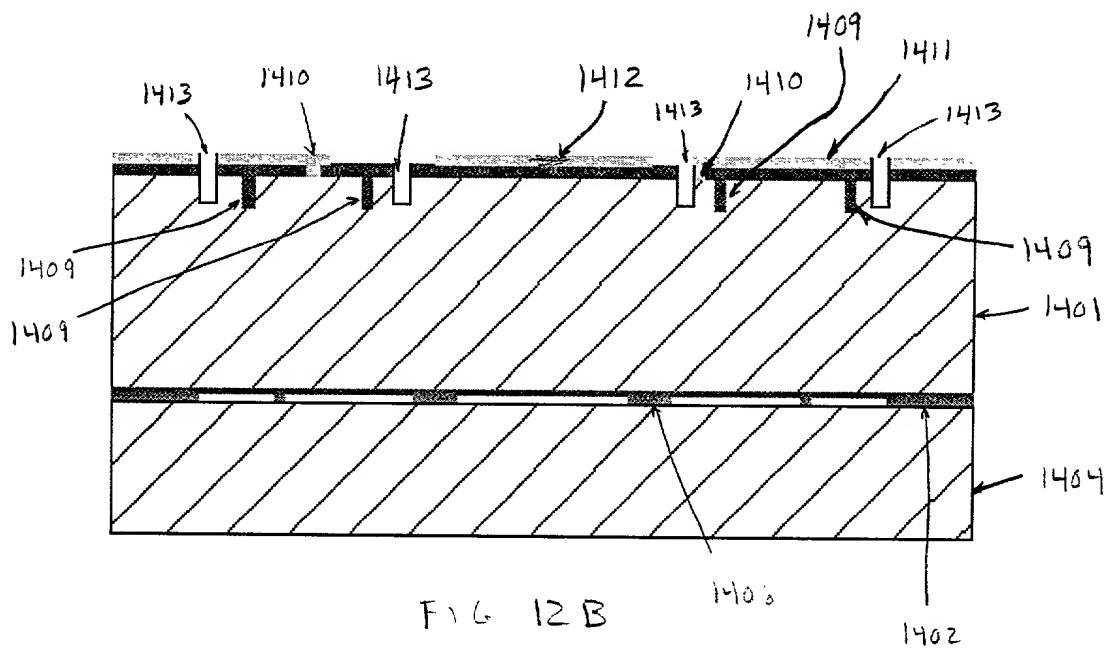
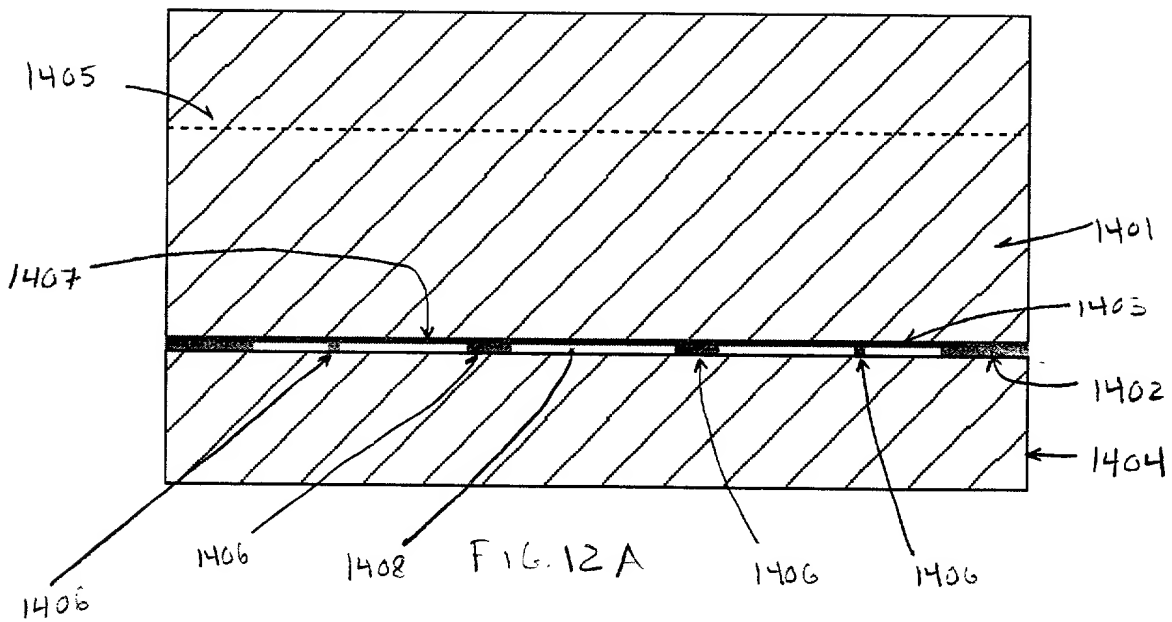


FIG. 10E







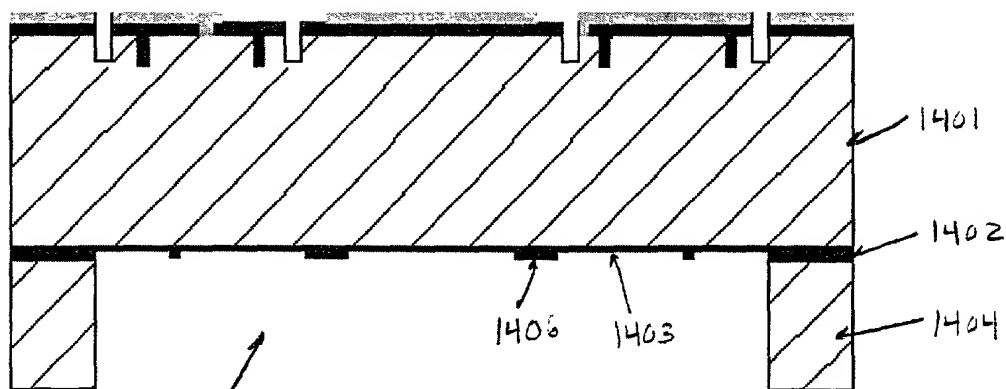


FIG. 12C

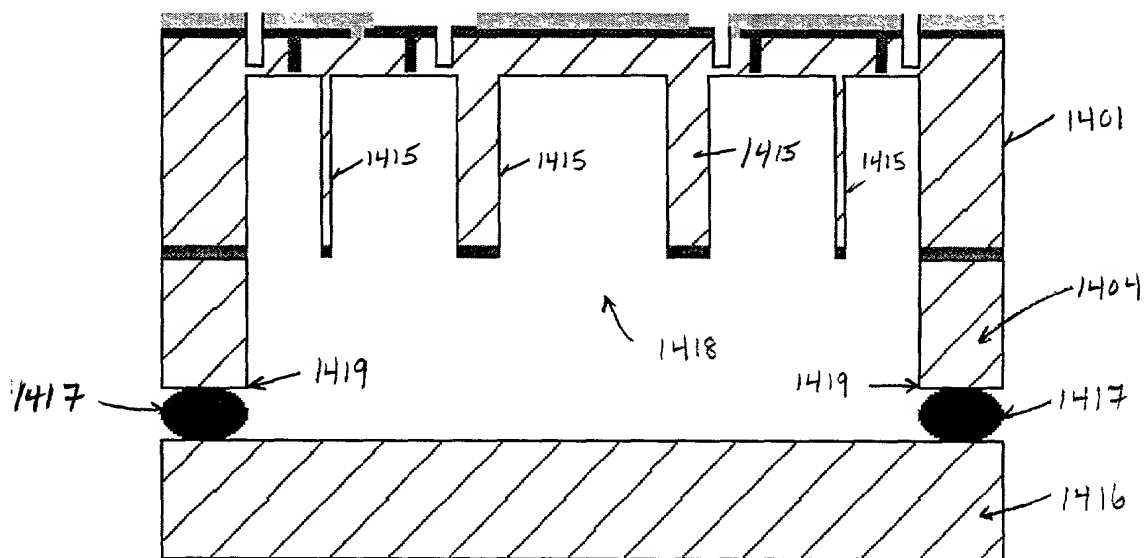


FIG. 12D

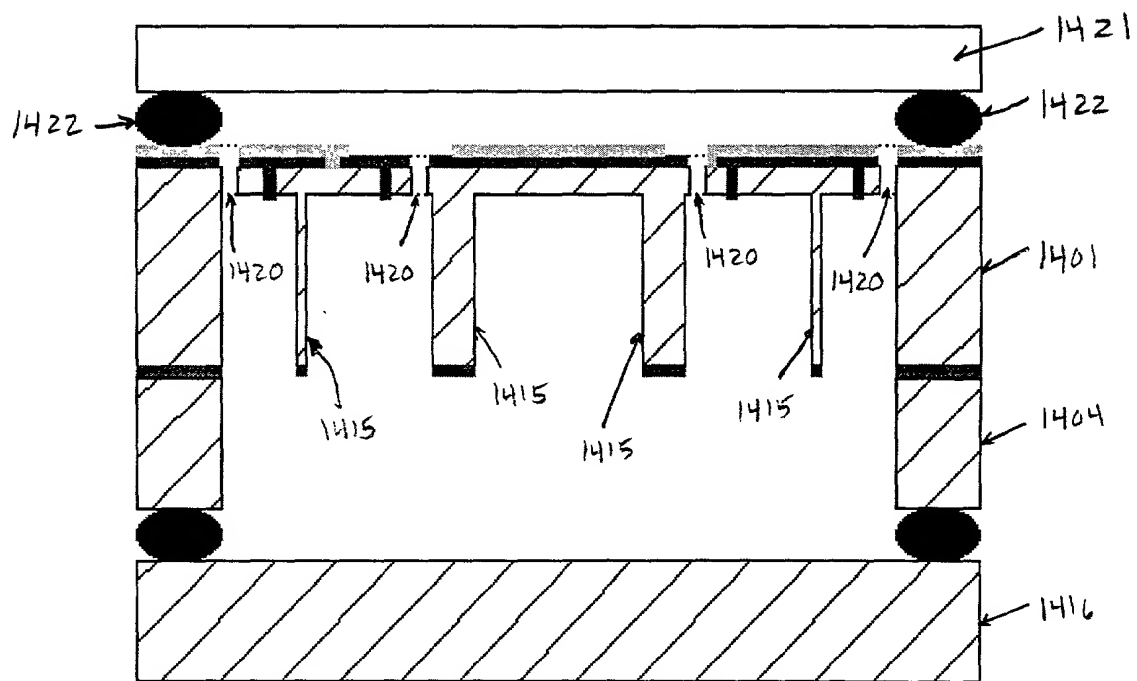


FIG 12E

FIG. 13A

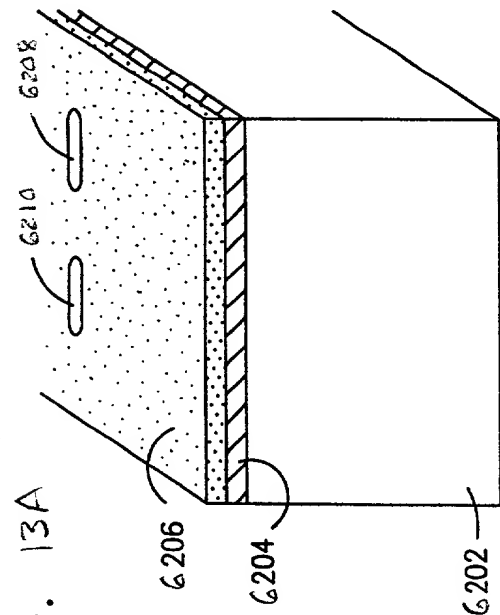


FIG. 13C

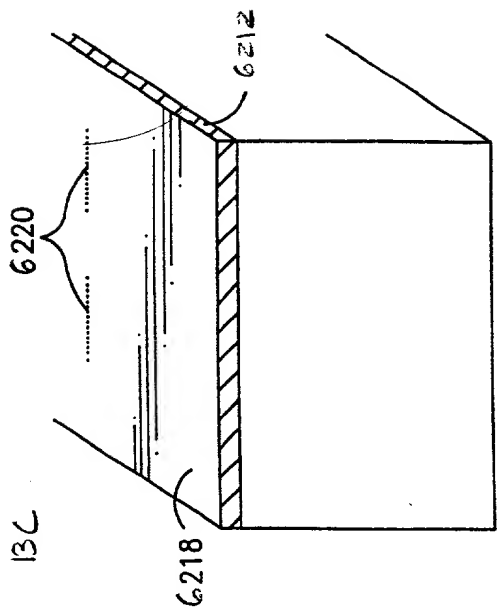


FIG. 13B

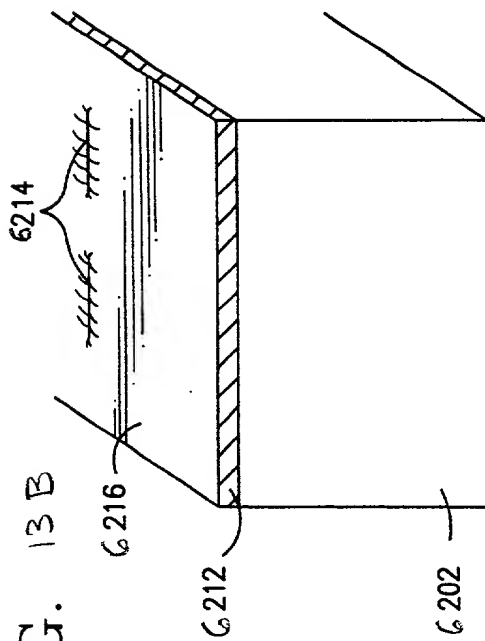


FIG. 13D

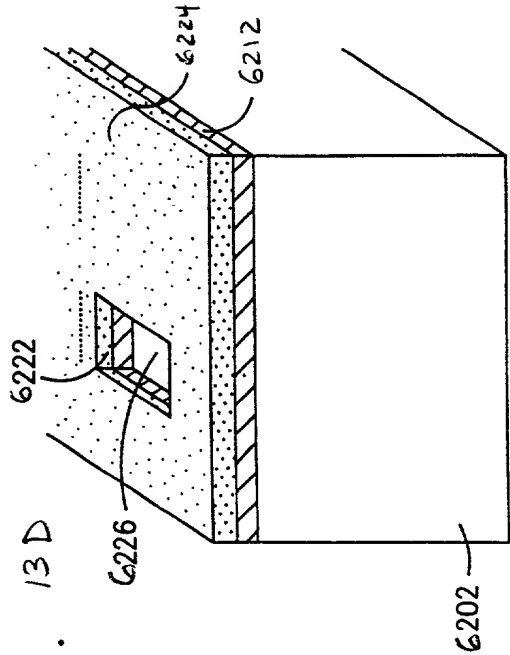


FIG. 13E

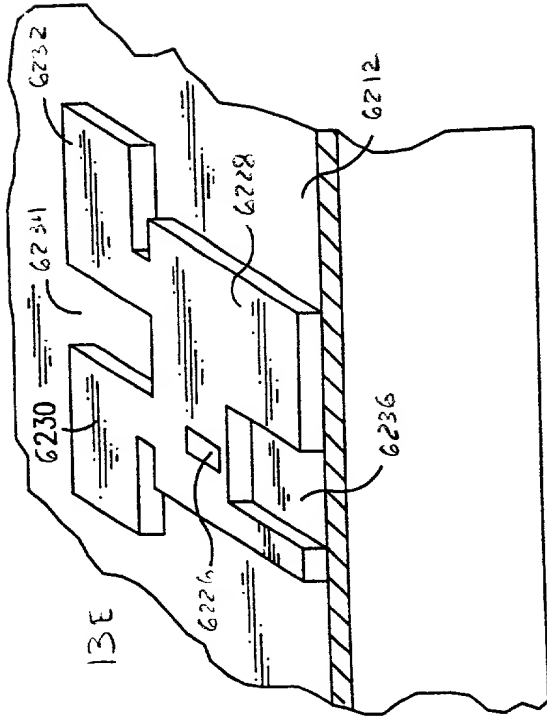


FIG. 13E

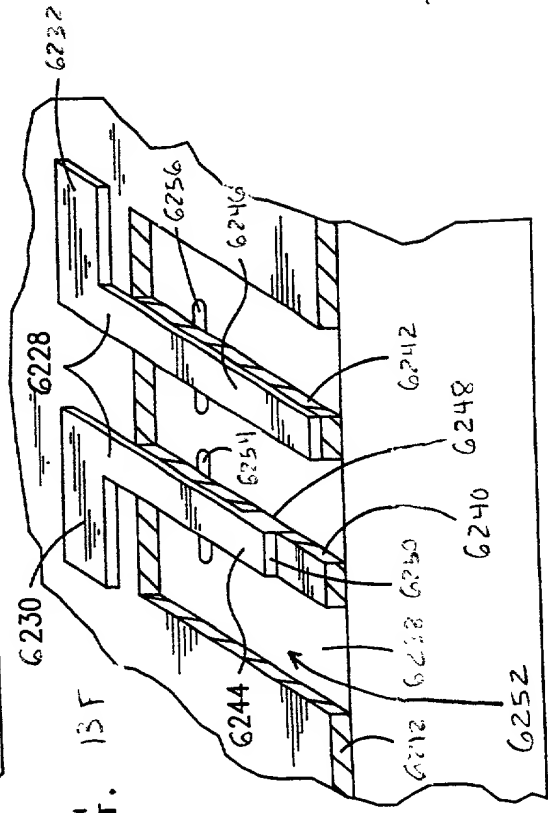


FIG. 13F

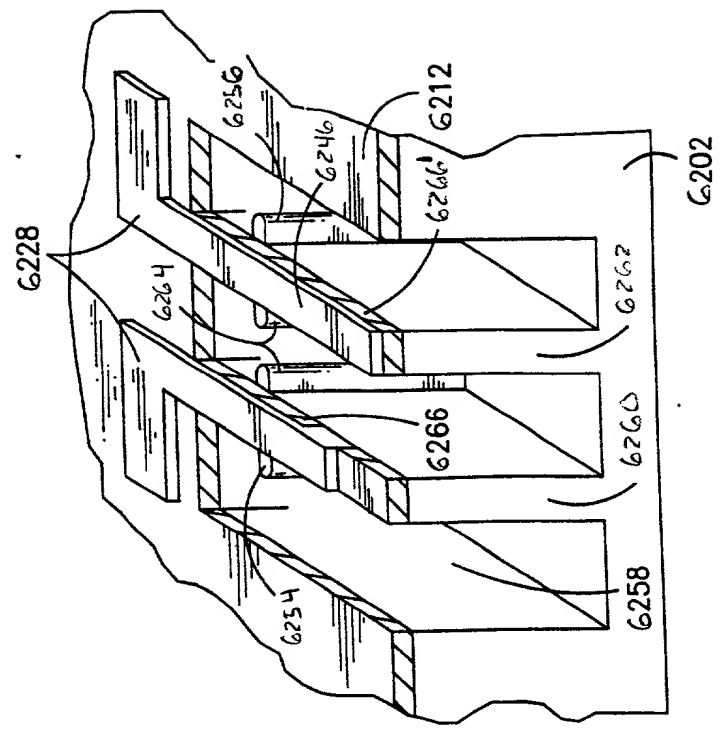


FIG. 13G

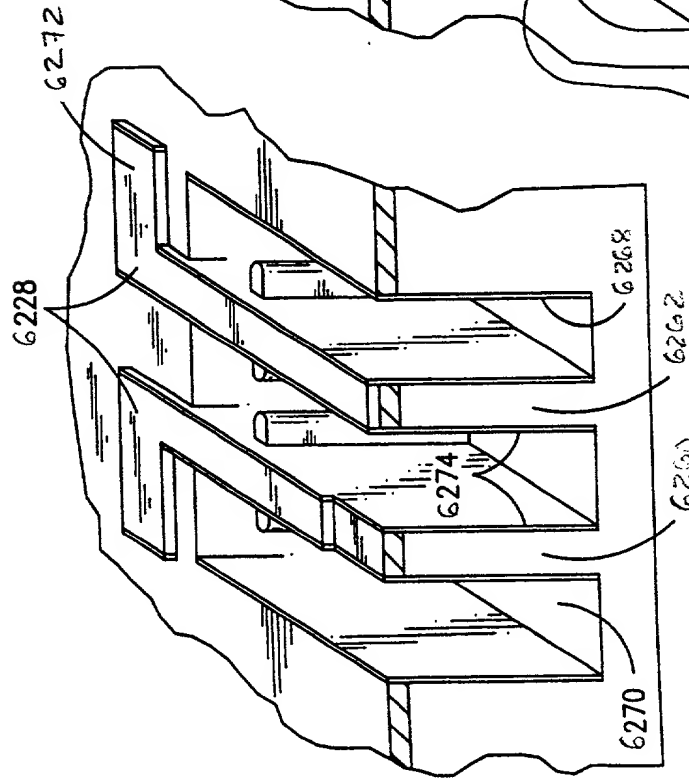


FIG. 13H

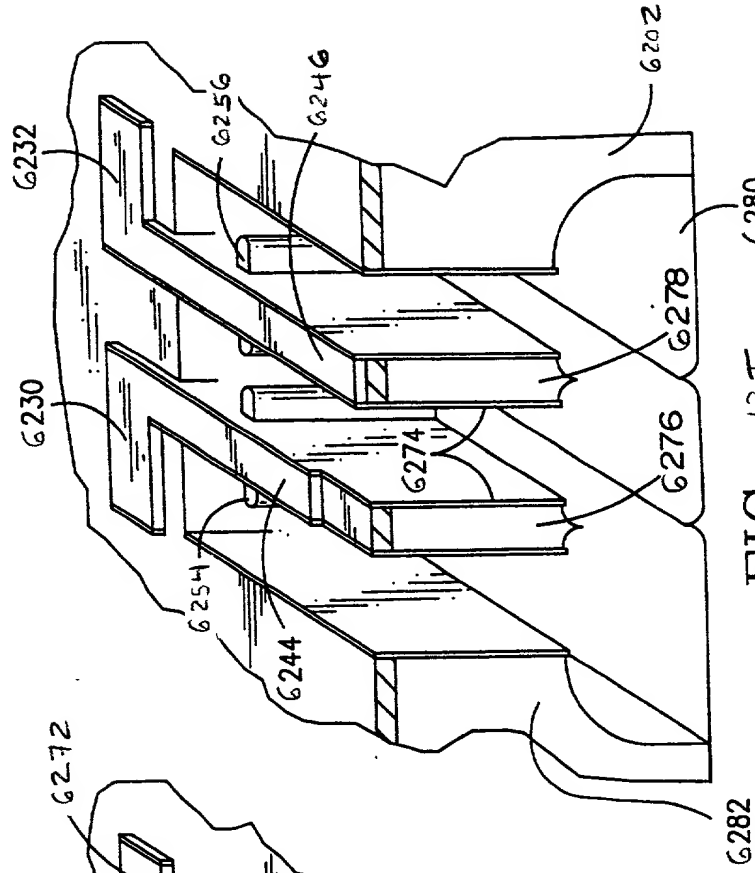


FIG. 13I